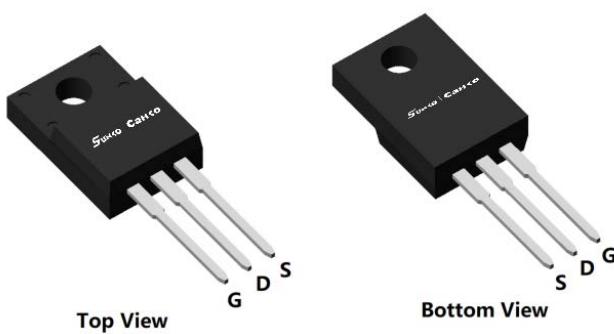
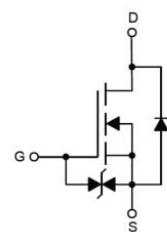


**N-Channel Enhancement Mode Field Effect Transistor**

Top View

Bottom View

ITO-220AB

**Product Summary**

- $V_{DS}$  150V
- $I_D$  15A
- $R_{DS(on)}$  (at  $V_{GS}=10V$ ) <70mΩ
- $R_{DS(on)}$  (at  $V_{GS}=6V$ ) <80mΩ
- 100% EAS Tested
- 100%  $\nabla V_{DS}$  Tested

**General Description**

- Split gate trench MOSFET technology
- Low  $R_{DS(on)}$  & FOM
- Excellent stability and uniformity
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

**Applications**

- Power management
- Portable equipment

**Absolute Maximum Ratings ( $T_A=25^\circ C$  unless otherwise noted)**

Parameter	Symbol	Limit	Units
Drain-source Voltage	$V_{DS}$	150	V
Gate-source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current	$I_D$	4	A
		2.5	
		15	
		9.5	
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	40	A
Avalanche energy <sup>B</sup>	EAS	4.4	mJ
Total Power Dissipation <sup>C</sup>	$P_D$	2.5	W
		1	
		41	
		16	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	°C

**Thermal resistance**

Parameter	Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient <sup>D</sup>	$R_{\theta JA}$	40	50	°C/W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	2.5	3	

**Ordering Information (Example)**

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
SCF15G15A	B1	SCF15G15A	50	/	5000	Tube

■ Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	150	-	-	V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=150\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	$\mu\text{A}$
		$V_{\text{DS}}=150\text{V}, V_{\text{GS}}=0\text{V}, T_J=150^\circ\text{C}$	-	-	100	
Gate-Body Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm 100$	nA
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	2	3	4	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=15\text{A}$	-	50	70	$\text{m}\Omega$
		$V_{\text{GS}}=6\text{V}, I_{\text{D}}=10\text{A}$	-	55	80	
Diode Forward Voltage	$V_{\text{SD}}$	$I_{\text{S}}=15\text{A}, V_{\text{GS}}=0\text{V}$	-	0.95	1.3	V
Gate resistance	$R_{\text{G}}$	$f=1\text{MHz}$	-	1.5	-	$\Omega$
Maximum Body-Diode Continuous Current	$I_{\text{S}}$		-	-	15	A
<b>Dynamic Parameters</b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=75\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$	-	785	-	$\text{pF}$
Output Capacitance	$C_{\text{oss}}$		-	55	-	
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	4	-	
<b>Switching Parameters</b>						
Total Gate Charge	$Q_{\text{g}}$	$V_{\text{GS}}=10\text{V}, V_{\text{DS}}=75\text{V}, I_{\text{D}}=7.5\text{A}$	-	18	-	$\text{nC}$
Gate-Source Charge	$Q_{\text{gs}}$		-	5	-	
Gate-Drain Charge	$Q_{\text{gd}}$		-	4.5	-	
Reverse Recovery Charge	$Q_{\text{rr}}$	$I_{\text{F}}=7.5\text{A}, \text{di/dt}=100\text{A/us}$	-	179	-	$\text{nC}$
Reverse Recovery Time	$t_{\text{rr}}$		-	53	-	ns
Turn-on Delay Time	$t_{\text{D}(\text{on})}$	$V_{\text{GS}}=10\text{V}, V_{\text{DD}}=75\text{V}, I_{\text{D}}=7.5\text{A}$ $R_{\text{GEN}}=2.2\Omega$	-	12	-	ns
Turn-on Rise Time	$t_{\text{r}}$		-	5	-	
Turn-off Delay Time	$t_{\text{D}(\text{off})}$		-	39	-	
Turn-off fall Time	$t_{\text{f}}$		-	6	-	

- A. Repetitive rating; pulse width limited by max. junction temperature.  
B.  $T_J=25^\circ\text{C}, V_{\text{DD}}=50\text{V}, V_{\text{G}}=10\text{V}, R_{\text{G}}=25\Omega, L=0.5\text{mH}, I_{\text{AS}}=4.2\text{A}$ .  
C.  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.  
D. The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in the still air environment with  $T_A=25^\circ\text{C}$ . The maximum allowed junction temperature of  $150^\circ\text{C}$ . The value in any given application depends on the user's specific board design.

## ■ Typical Electrical and Thermal Characteristics Diagrams

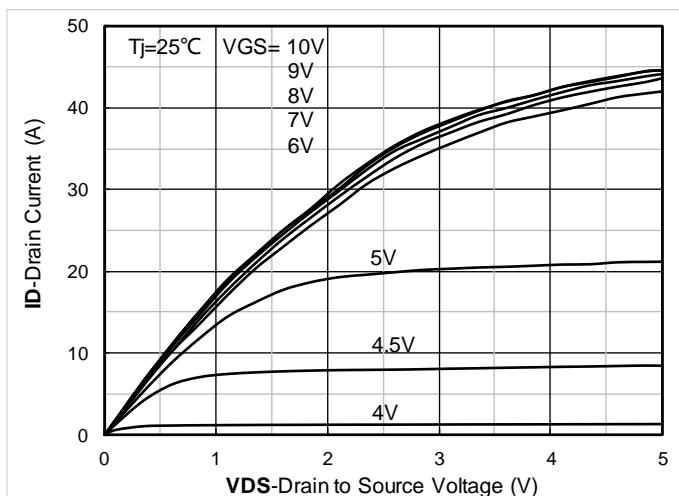


Figure 1. Output Characteristics

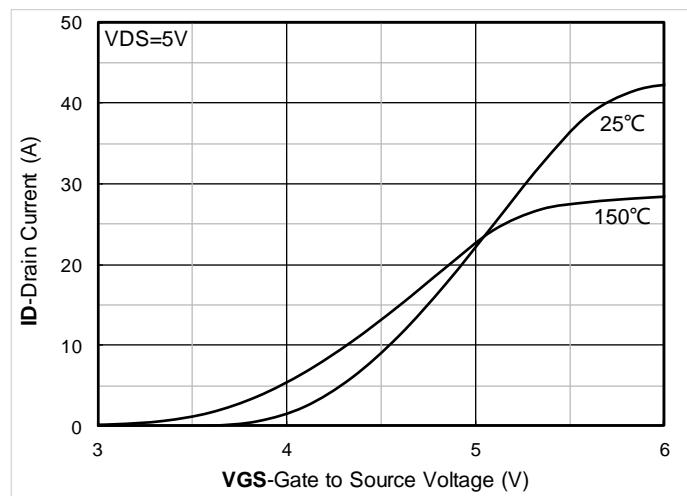


Figure 2. Transfer Characteristics

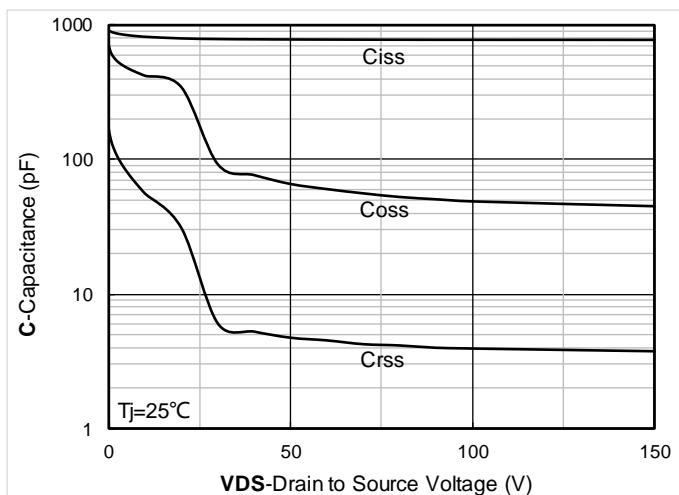


Figure 3. Capacitance Characteristics

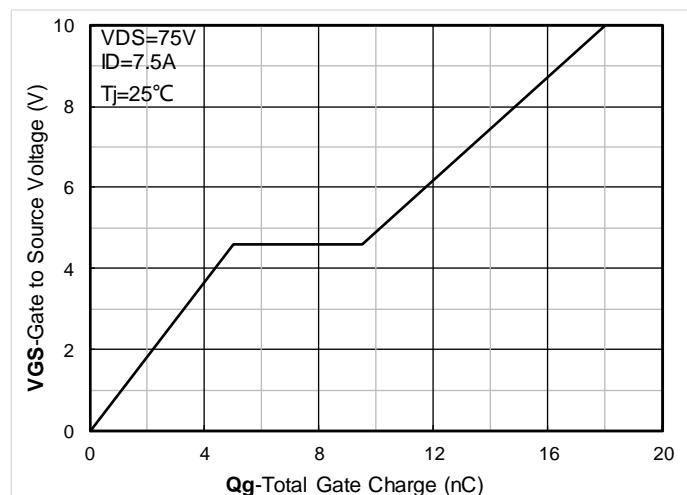


Figure 4. Gate Charge

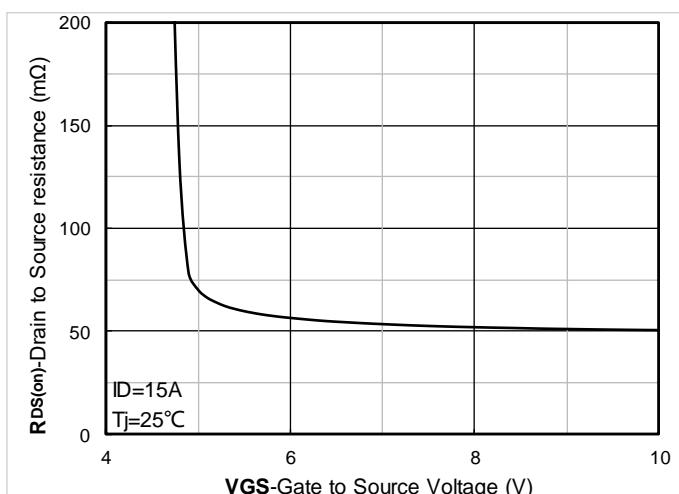


Figure 5. On-Resistance vs Gate to Source Voltage

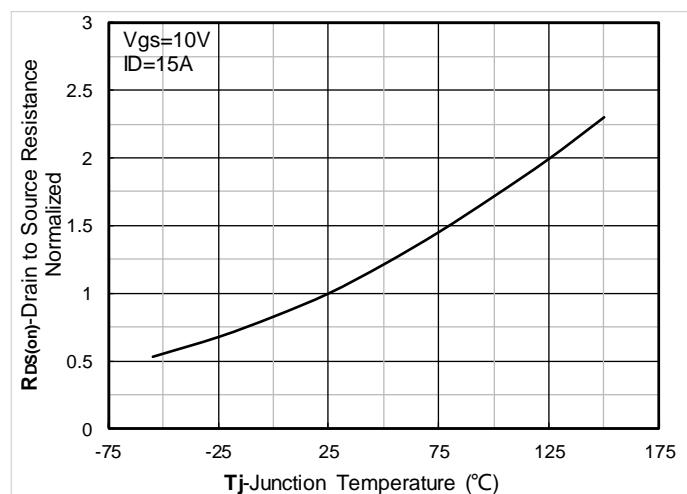


Figure 6. Normalized On-Resistance

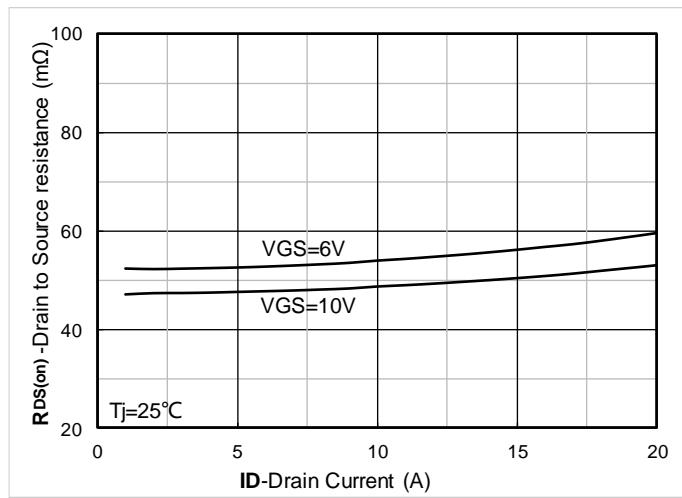


Figure 7. RDS(on) VS Drain Current

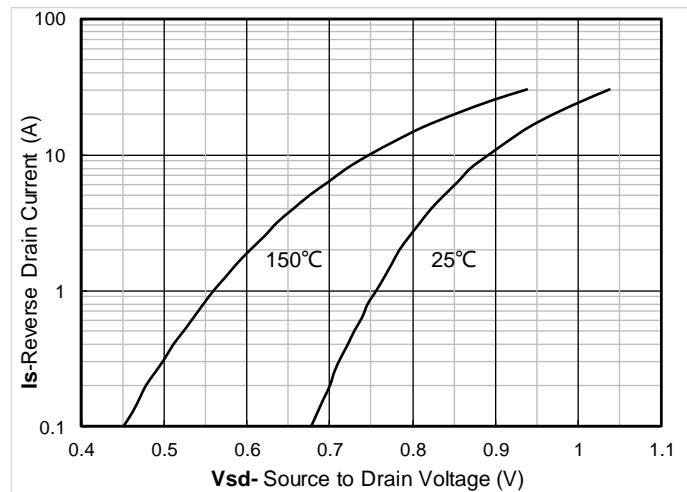


Figure 8. Forward characteristics of reverse diode

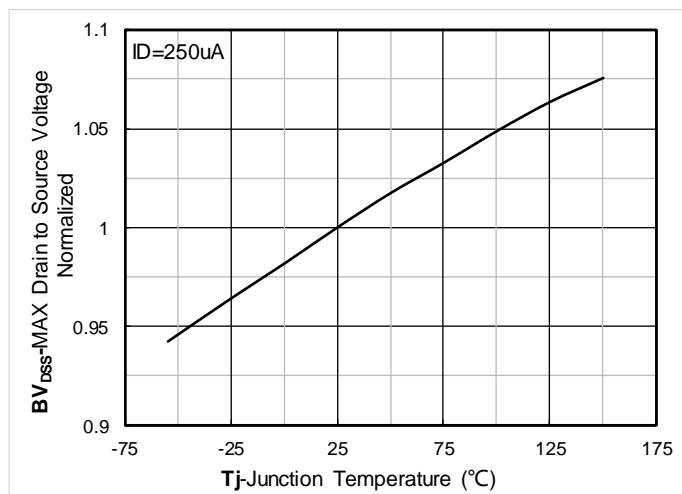


Figure 9. Normalized breakdown voltage

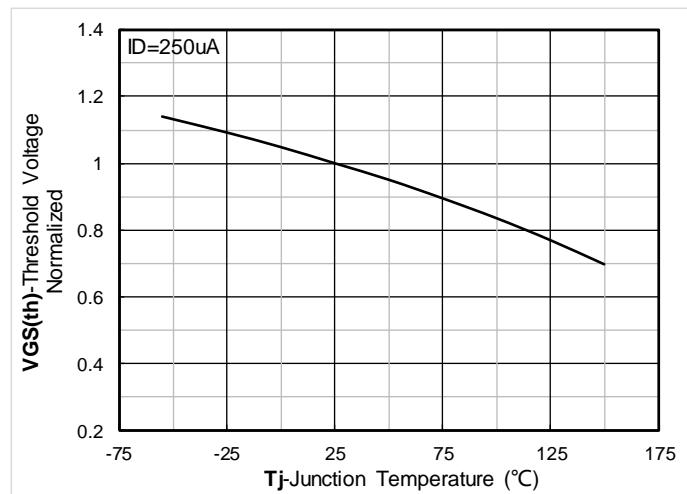


Figure 10. Normalized Threshold voltage

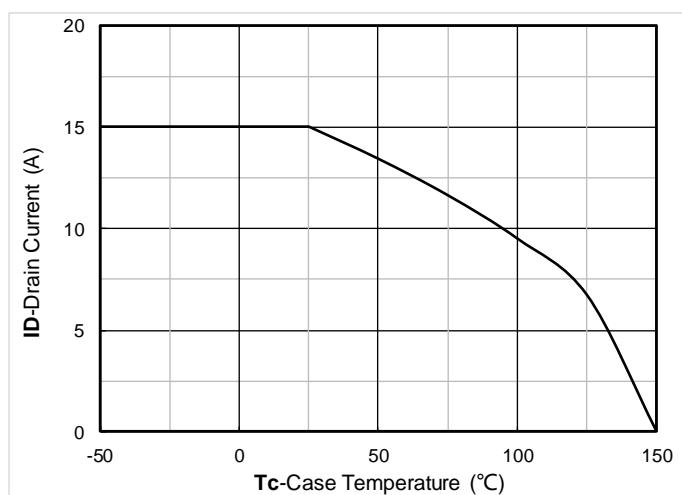


Figure 11. Current dissipation

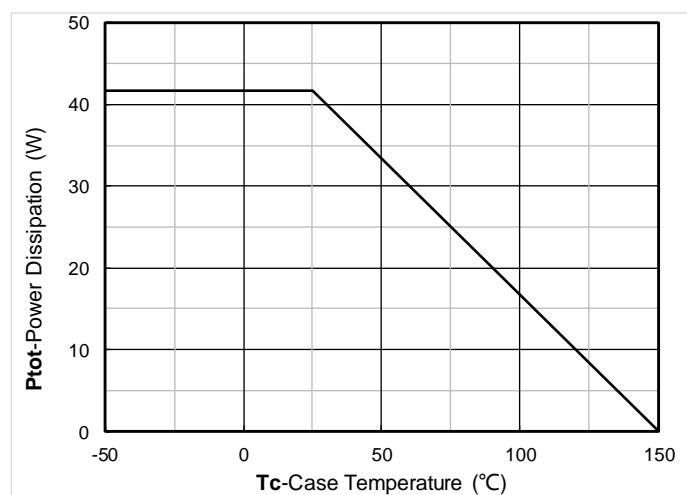


Figure 12. Power dissipation

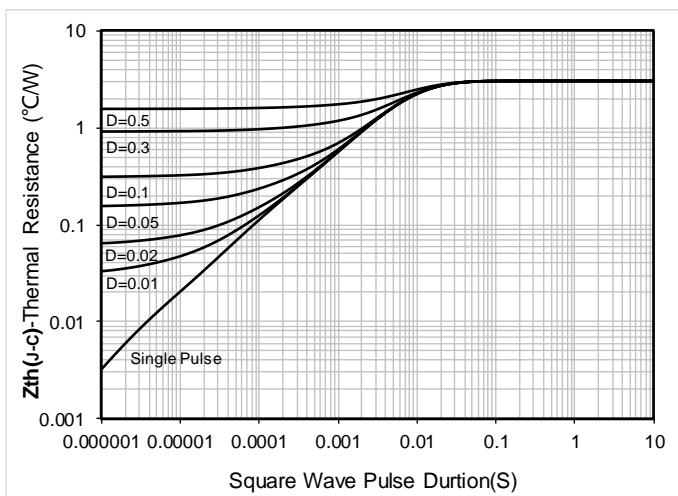


Figure 13. Maximum Transient Thermal Impedance

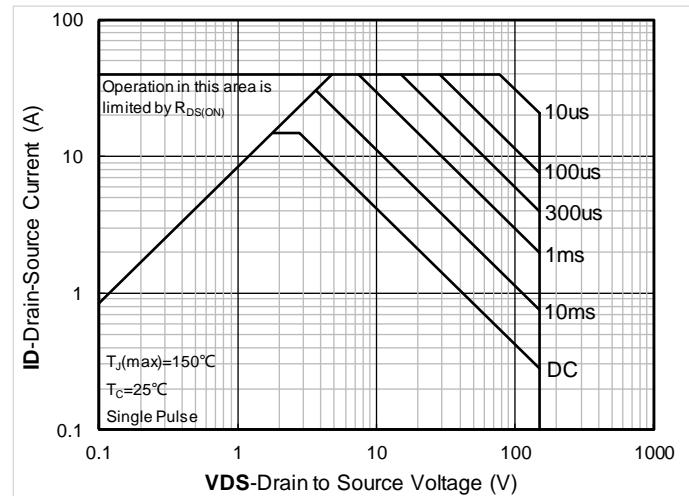


Figure 14. Safe Operation Area

## ■ Test Circuits & Waveforms

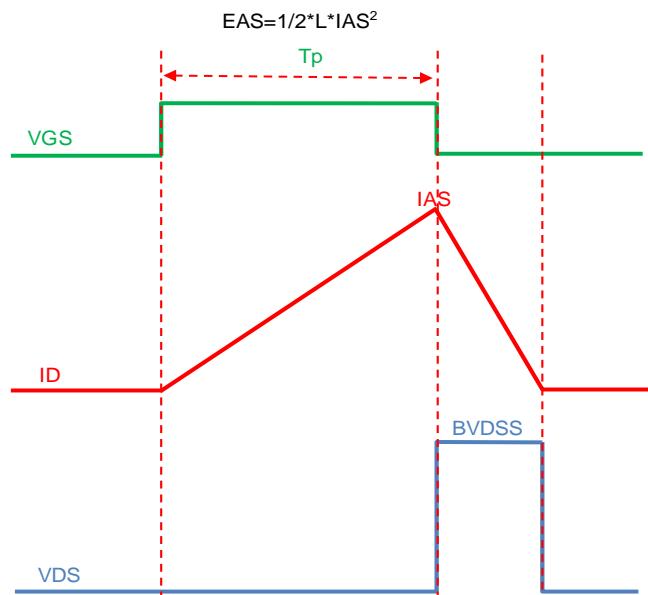
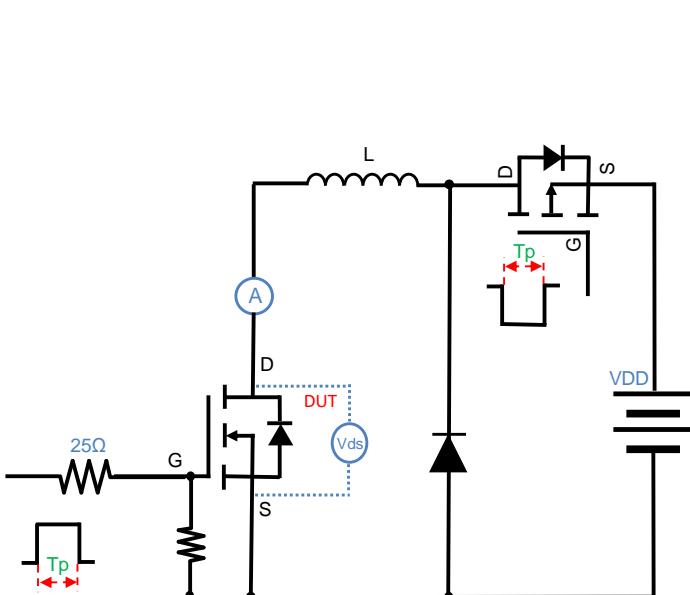


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

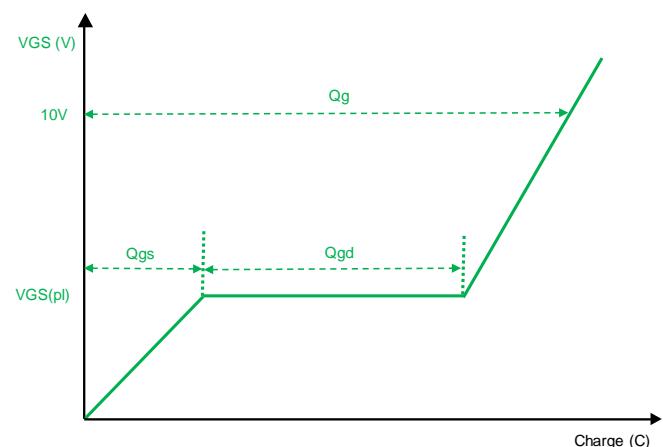
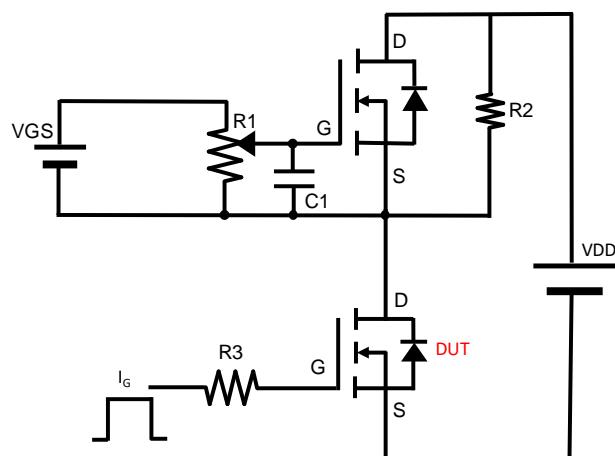


Figure B. Gate Charge Test Circuit &amp; Waveform

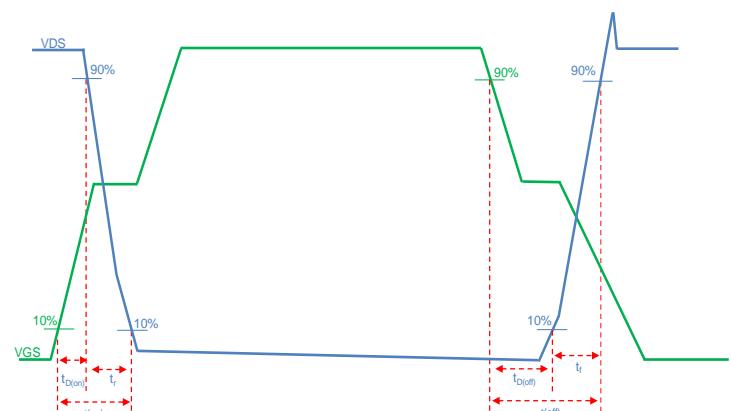
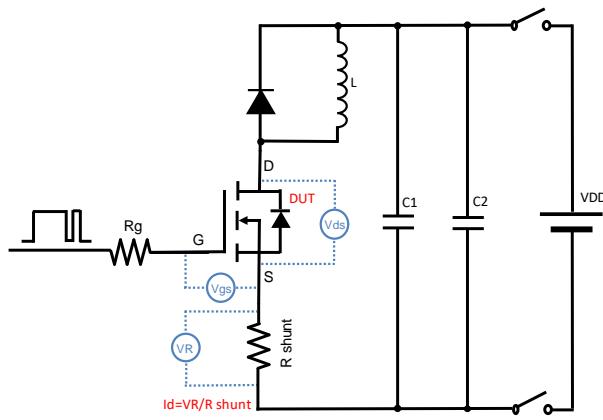


Figure C. Resistive Switching Test Circuit &amp; Waveform

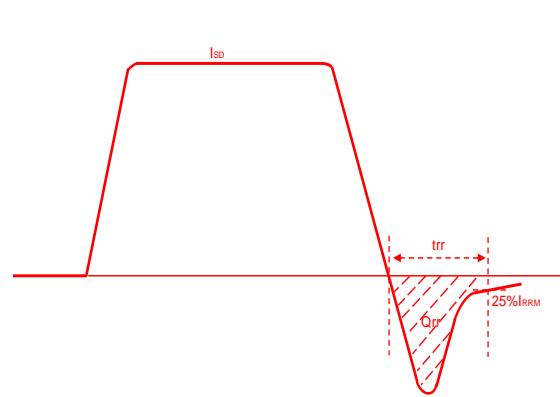
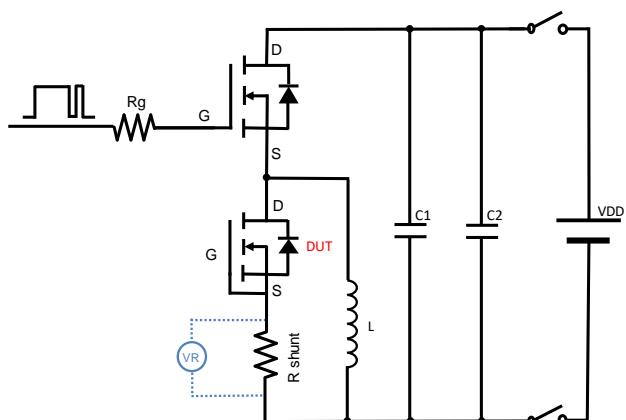
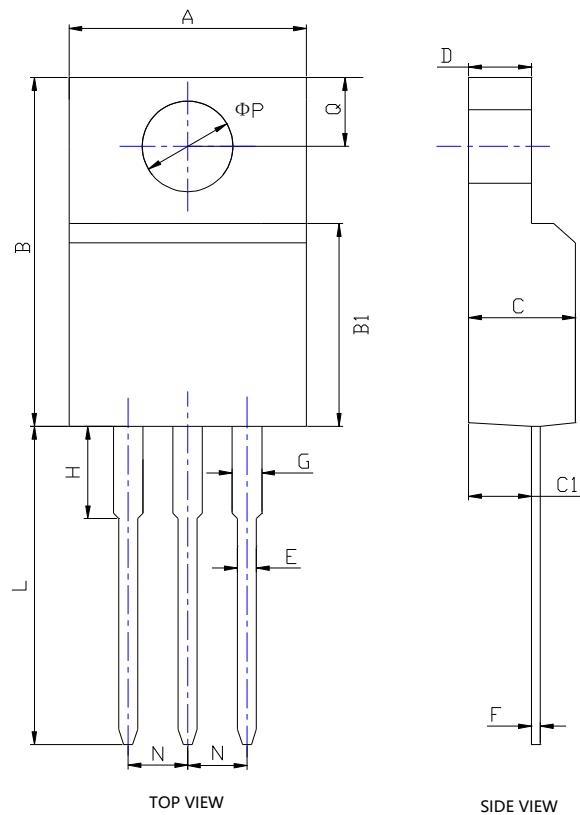


Figure D. Diode Recovery Test Circuit &amp; Waveform

## ■ ITO-220AB-B Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.382	0.406	9.700	10.300
B	0.610	0.634	15.500	16.100
B1	0.354	0.370	8.990	9.390
C	0.173	0.189	4.400	4.800
C1	0.085	0.100	2.150	2.550
D	0.098	0.114	2.500	2.900
E	0.028	0.035	0.700	0.900
F	0.016	0.024	0.400	0.600
G	0.044	0.056	1.120	1.420
H	0.134	0.150	3.400	3.800
L	0.496	0.535	12.600	13.600
N	0.092	0.108	2.340	2.740
Q	0.124	0.140	3.150	3.550
ΦP	0.118	0.130	3.000	3.300

### NOTE:

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.

**Disclaimer**

The information presented in this document is for reference only. Shanghai Sunco Electronics Co., Ltd reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices). Russiansunco or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <http://www.russiansunco.co> or consult your nearest Russiansunco's sales office for further assistance.